Preliminary datasheet
EconoPIM™2 module with TRENCHSTOP™IGBT7 and emitter controlled 7 diode and NTC

Features

Typical appearance

- Electrical features
  - V_{CES} = 1200 V
  - $I_{C\ nom}$ = 100 A / I_{CRM} = 200 A
  - Low V_{CEsat}
  - Overload operation up to 175°C
  - TRENCHSTOP™ IGBT7
- Mechanical features
  - Al_2O_3 substrate with low thermal resistance
  - Copper base plate
  - Integrated NTC temperature sensor
  - PressFIT contact technology

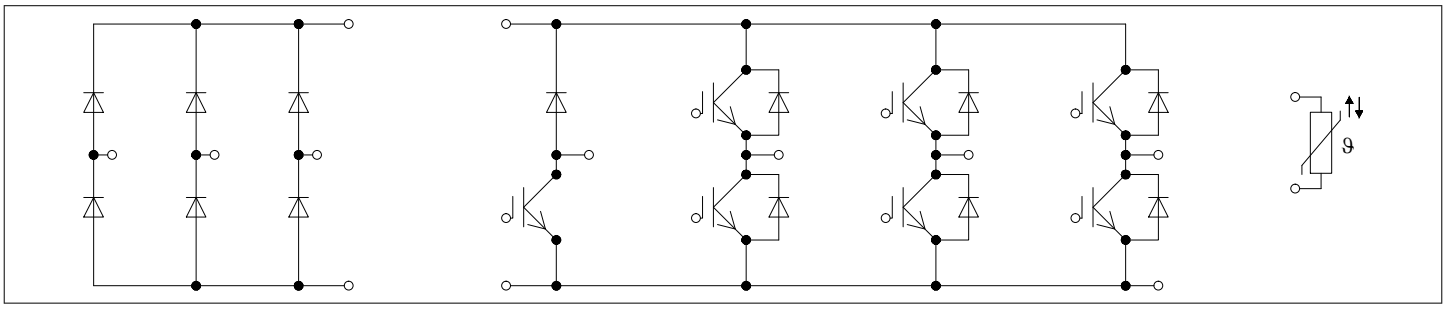
Potential applications

- Servo drives
- Auxiliary inverters
- Motor drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description



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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, *t* = 1 min	2.5	kV
Material of module baseplate			Cu	
Internal Isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to heatsink	7.5	mm
Comparative tracking index	*CTI*		> 200	
RTI Elec.	*RTI*	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Stray inductance module	L_{sCE}				35		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	T_C=25°C, per switch			2.5		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	T_C=25°C, per switch			4.3		mΩ
Storage temperature	T_{stg}			-40		125	°C
Mounting torque for modul mounting	*M*	- Mounting according to valid application note	M5, Screw	3		6	Nm
Weight	*G*				180		g

Note: The current under continuous operation is limited to 80A rms in the main AC and DC power terminals and limited to 50A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		T_{vj} = 25 °C	1200	V
Continous DC collector current	I_{CDC}	$T_{vj\,max}$ = 175 °C	T_C = 95 °C	100	A
Repetitive peak collector current	I_{CRM}	t_P = 1 ms		200	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\,sat}$	I_C = 100 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.50	TBD	V
			T_{vj} = 125 °C		1.64		
			T_{vj} = 175 °C		1.72		
Gate threshold voltage	V_{GEth}	I_C = 2.5 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		5.15	5.80	6.45	V
Gate charge	Q_G	V_{GE} = ±15 V, V_{CE} = 600 V			1.8		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			1.5		Ω
Input capacitance	C_{ies}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			21.7		nF
Reverse transfer capacitance	C_{res}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			0.076		nF
Collector-emitter cut-off current	I_{CES}	V_{CE} = 1200 V, V_{GE} = 0 V	T_{vj} = 25 °C			0.01	mA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25 °C				100	nA
Turn-on delay time (inductive load)	t_{don}	I_C = 100 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Gon} = 4.3 Ω	T_{vj} = 25 °C		0.171		µs
			T_{vj} = 125 °C		0.185		
			T_{vj} = 175 °C		0.190		
Rise time (inductive load)	t_r	I_C = 100 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Gon} = 4.3 Ω	T_{vj} = 25 °C		0.050		µs
			T_{vj} = 125 °C		0.055		
			T_{vj} = 175 °C		0.058		
Turn-off delay time (inductive load)	t_{doff}	I_C = 100 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Goff} = 4.3 Ω	T_{vj} = 25 °C		0.324		µs
			T_{vj} = 125 °C		0.433		
			T_{vj} = 175 °C		0.494		
Fall time (inductive load)	t_f	I_C = 100 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Goff} = 4.3 Ω	T_{vj} = 25 °C		0.093		µs
			T_{vj} = 125 °C		0.183		
			T_{vj} = 175 °C		0.245		
Turn-on energy loss per pulse	E_{on}	I_C = 100 A, V_{CE} = 600 V, L_σ = 35 nH, V_{GE} = ±15 V, R_{Gon} = 4.3 Ω, di/dt = 1450 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		10.4		mJ
			T_{vj} = 125 °C		15.3		
			T_{vj} = 175 °C		17.6		
Turn-off energy loss per pulse	E_{off}	I_C = 100 A, V_{CE} = 600 V, L_σ = 35 nH, V_{GE} = ±15 V, R_{Goff} = 4.3 Ω, dv/dt = 2850 V/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		6.42		mJ
			T_{vj} = 125 °C		9.95		
			T_{vj} = 175 °C		12.3		
SC data	I_{SC}	V_{GE} ≤ 15 V, V_{CC} = 800 V, V_{CEmax}=V_{CES}-L_{sCE}*di/dt	t_P ≤ 8 µs, T_{vj} = 150 °C		370		A
			t_P ≤ 7 µs, T_{vj} = 175 °C		350		

Table 4 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.371	K/W
Thermal resistance, case to heatsink	R_{thCH}	per IGBT, λ_{grease}= 1 W/(m*K)		0.135		K/W
Temperature under switching conditions	$T_{vj\,op}$		-40		175	°C

Note: $T_{vj\,op}$ > 150°C is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	1200	V
Continous DC forward current	I_F			100	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		200	A
I^2t - value	I^2t	t_P = 10 ms, V_R = 0 V	T_{vj} = 125 °C	1000	A^2s
			T_{vj} = 175 °C	930	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 100 A, V_{GE} = 0 V	T_{vj} = 25 °C		1.72	TBD	V
			T_{vj} = 125 °C		1.59		
			T_{vj} = 175 °C		1.52		
Peak reverse recovery current	I_{RM}	V_R = 600 V, I_F = 100 A, V_{GE} = -15 V, -di_F/dt = 1450 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		58.2		A
			T_{vj} = 125 °C		74.3		
			T_{vj} = 175 °C		82.4		
Recovered charge	Q_r	V_R = 600 V, I_F = 100 A, V_{GE} = -15 V, -di_F/dt = 1450 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		9.83		µC
			T_{vj} = 125 °C		15.9		
			T_{vj} = 175 °C		20.1		

Table 6 Characteristic values (continued)

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Reverse recovery energy	E_{rec}	V_R = 600 V, I_F = 100 A, V_{GE} = -15 V, -di$_F$/dt = 1450 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		3.31		mJ
			T_{vj} = 125 °C		5.01		
			T_{vj} = 175 °C		6.45		
Thermal resistance, junction to case	R_{thJC}	per diode				0.592	K/W
Thermal resistance, case to heatsink	R_{thCH}	per diode, λ_{grease}= 1 W/(m*K)			0.148		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C

Note: $T_{vj\,op}$ > 150°C is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

4 Diode, Rectifier

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}	T_{vj} = 25 °C		1600	V
Maximum RMS forward current per chip	I_{FRMSM}	T_C = 110 °C		100	A
Maximum RMS current at rectifier output	I_{RMSM}	T_C = 110 °C		100	A
Surge forward current	I_{FSM}	t_P = 10 ms	T_{vj} = 25 °C	745	A
			T_{vj} = 150 °C	515	
I²t - value	I^2t	t_P = 10 ms	T_{vj} = 25 °C	2780	A²s
			T_{vj} = 150 °C	1330	

Table 8 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 100 A	T_{vj} = 150 °C		1.16		V
Reverse current	I_r	T_{vj} = 150 °C, V_R = 1600 V			1		mA
Thermal resistance, junction to case	R_{thJC}	per diode				0.697	K/W
Thermal resistance, case to heatsink	R_{thCH}	per diode, λ_{grease}= 1 W/(m*K)			0.153		K/W

Table 8 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Temperature under switching conditions	$T_{vj, op}$		-40		150	°C

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Table 9 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		T_{vj} = 25 °C	1200	V
Continous DC collector current	I_{CDC}	$T_{vj\,max}$ = 175 °C	T_C = 115 °C	50	A
Repetitive peak collector current	I_{CRM}	t_P = 1 ms		100	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 10 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\,sat}$	I_C = 50 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.50	TBD	V
			T_{vj} = 125 °C		1.64		
			T_{vj} = 175 °C		1.72		
Gate threshold voltage	V_{GEth}	I_C = 1.28 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		5.15	5.80	6.45	V
Gate charge	Q_G	V_{GE} = ±15 V, V_{CE} = 600 V			0.92		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			0		Ω
Input capacitance	C_{ies}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			11.1		nF
Reverse transfer capacitance	C_{res}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			0.039		nF
Collector-emitter cut-off current	I_{CES}	V_{CE} = 1200 V, V_{GE} = 0 V	T_{vj} = 25 °C			0.008	mA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25 °C				100	nA
Turn-on delay time (inductive load)	t_{don}	I_C = 50 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Gon} = 8.2 Ω	T_{vj} = 25 °C		0.060		µs
			T_{vj} = 125 °C		0.062		
			T_{vj} = 175 °C		0.063		
Rise time (inductive load)	t_r	I_C = 50 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Gon} = 8.2 Ω	T_{vj} = 25 °C		0.036		µs
			T_{vj} = 125 °C		0.040		
			T_{vj} = 175 °C		0.042		

Table 10 Characteristic values (continued)

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off delay time (inductive load)	t_{doff}	I_C = 50 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Goff} = 8.2 Ω	T_{vj} = 25 °C		0.290		µs
			T_{vj} = 125 °C		0.380		
			T_{vj} = 175 °C		0.420		
Fall time (inductive load)	t_f	I_C = 50 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Goff} = 8.2 Ω	T_{vj} = 25 °C		0.110		µs
			T_{vj} = 125 °C		0.200		
			T_{vj} = 175 °C		0.270		
Turn-on energy loss per pulse	E_{on}	I_C = 50 A, V_{CE} = 600 V, L_σ = 35 nH, V_{GE} = ±15 V, R_{Gon} = 8.2 Ω, di/dt = 800 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		5.35		mJ
			T_{vj} = 125 °C		7.04		
			T_{vj} = 175 °C		8		
Turn-off energy loss per pulse	E_{off}	I_C = 50 A, V_{CE} = 600 V, L_σ = 35 nH, V_{GE} = ±15 V, R_{Goff} = 8.2 Ω, dv/dt = 2900 V/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		3.33		mJ
			T_{vj} = 125 °C		5.32		
			T_{vj} = 175 °C		6.58		
SC data	I_{SC}	V_{GE} ≤ 15 V, V_{CC} = 800 V, V_{CEmax}=V_{CES}-L_{sCE}*di/dt	t_P ≤ 8 µs, T_{vj} = 150 °C		190		A
			t_P ≤ 7 µs, T_{vj} = 175 °C		180		
Thermal resistance, junction to case	R_{thJC}	per IGBT				0.580	K/W
Thermal resistance, case to heatsink	R_{thCH}	per IGBT, λ_{grease}= 1 W/(m*K)			0.147		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C

Note: $T_{vj\,op}$ > 150°C is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

6 Diode, Brake-Chopper

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	1200	V
Continous DC forward current	I_F			35	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		70	A

Table 11 Maximum rated values (continued)

Parameter	Symbol	Note or test condition		Values	Unit
I^2t - value	I^2t	t_P = 10 ms, V_R = 0 V	T_{vj} = 150 °C	125	A^2s
			T_{vj} = 175 °C	95	

Table 12 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 35 A, V_{GE} = 0 V	T_{vj} = 25 °C		1.72	TBD	V
			T_{vj} = 125 °C		1.59		
			T_{vj} = 175 °C		1.52		
Peak reverse recovery current	I_{RM}	V_R = 600 V, I_F = 35 A, V_{GE} = -15 V, -di$_F$/dt = 700 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		20.1		A
			T_{vj} = 125 °C		25.9		
			T_{vj} = 175 °C		29.8		
Recovered charge	Q_r	V_R = 600 V, I_F = 35 A, V_{GE} = -15 V, -di$_F$/dt = 700 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		2.66		µC
			T_{vj} = 125 °C		4.73		
			T_{vj} = 175 °C		6.94		
Reverse recovery energy	E_{rec}	V_R = 600 V, I_F = 35 A, V_{GE} = -15 V, -di$_F$/dt = 700 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		0.95		mJ
			T_{vj} = 125 °C		1.72		
			T_{vj} = 175 °C		2.38		
Thermal resistance, junction to case	R_{thJC}	per diode				1.11	K/W
Thermal resistance, case to heatsink	R_{thCH}	per diode, λ_{grease}= 1 W/(m*K)			0.176		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C

Note: $T_{vj\,op}$ > 150°C is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

7 NTC-Thermistor

Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	T_{NTC} = 25 °C		5		kΩ
Deviation of R_{100}	$\Delta R/R$	T_{NTC} = 100 °C, R_{100} = 493 Ω	-5		5	%
Power dissipation	P_{25}	T_{NTC} = 25 °C			20	mW

Table 13 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2\text{-}1/(298{,}15\ K))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2\text{-}1/(298{,}15\ K))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2\text{-}1/(298{,}15\ K))]$		3433		K

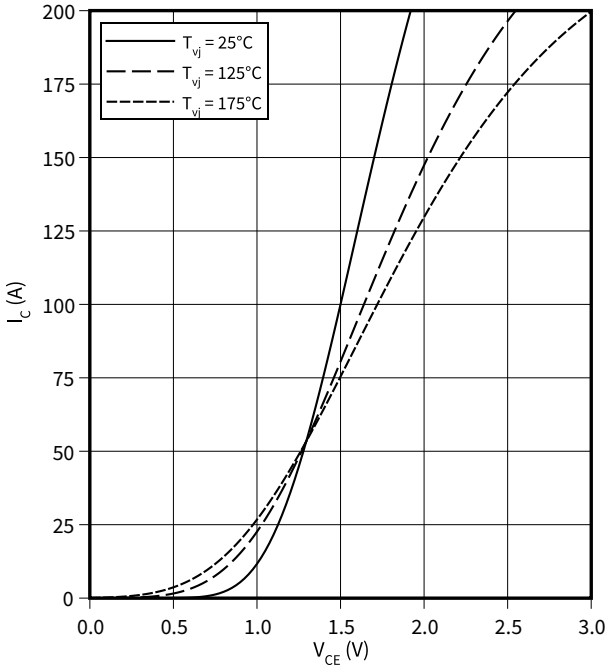
Note: Specification according to the valid application note.

8 Characteristics diagrams

output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

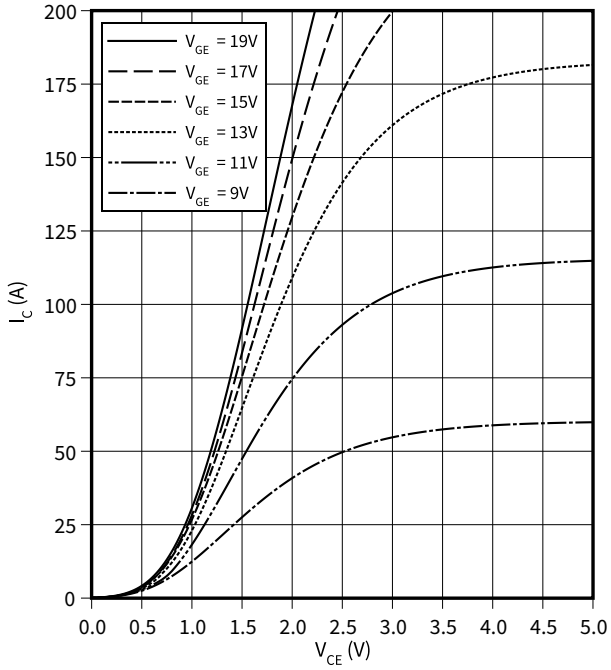
V_{GE} = 15 V



output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

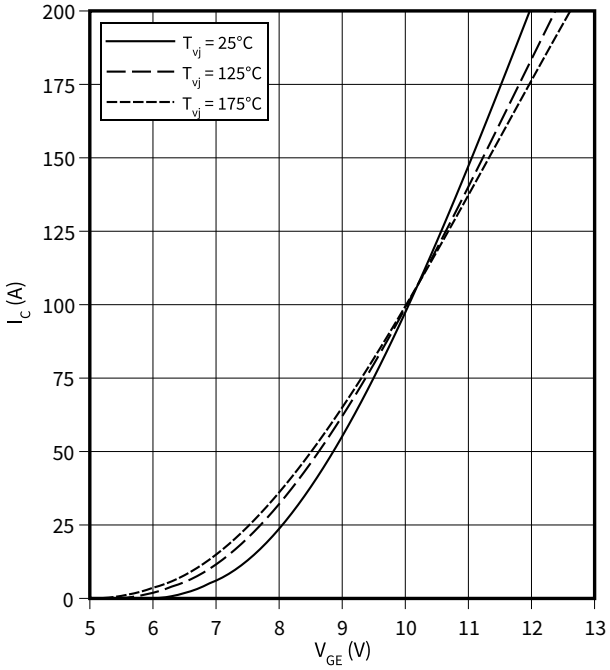
T_{vj} = 175 °C



transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

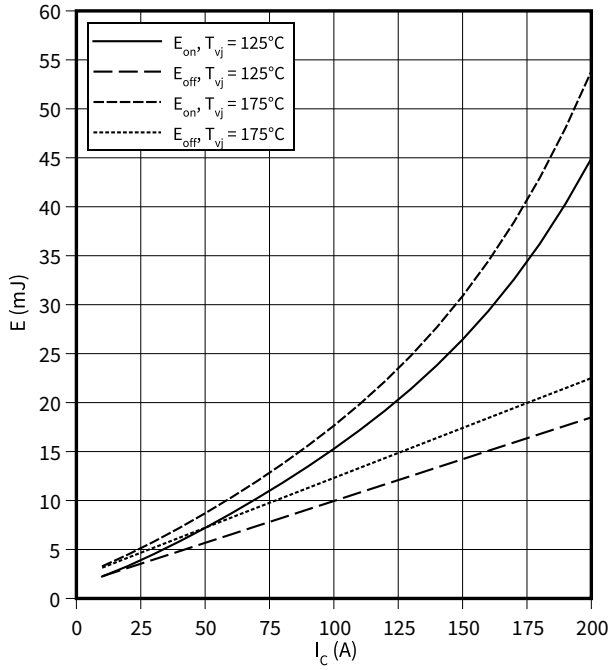
V_{CE} = 20 V



switching losses (typical), IGBT, Inverter

$E = f(I_C)$

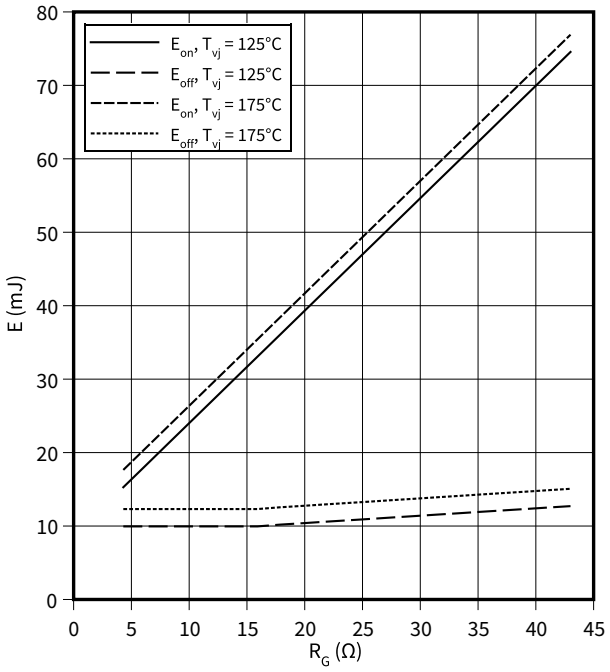
R_{Goff} = 4.3 Ω, R_{Gon} = 4.3 Ω, V_{CE} = 600 V, V_{GE} = ± 15 V



switching losses (typical), IGBT, Inverter

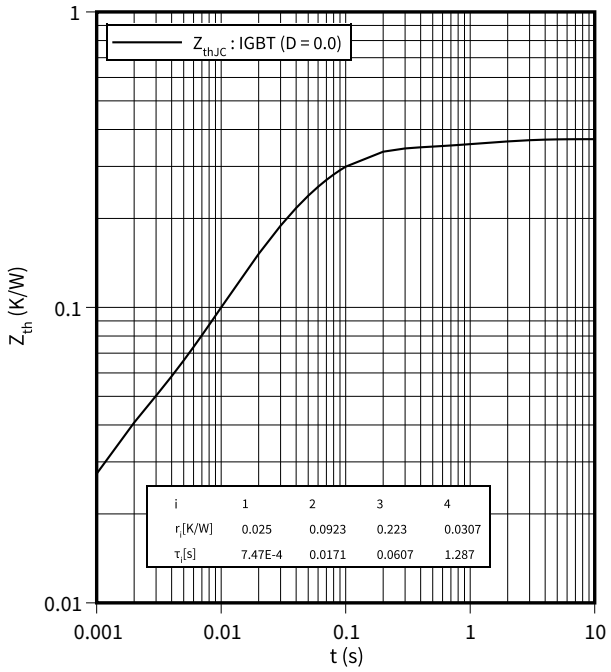
$E = f(R_G)$

$I_C = 100\ A$, $V_{CE} = 600\ V$, $V_{GE} = \pm 15\ V$



transient thermal impedance , IGBT, Inverter

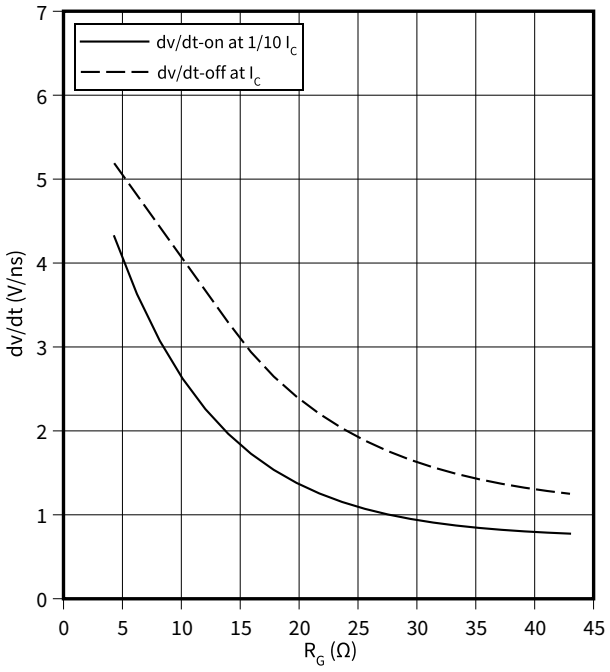
$Z_{th} = f(t)$



Voltage slope (typical), IGBT, Inverter

$dv/dt = f(R_G)$

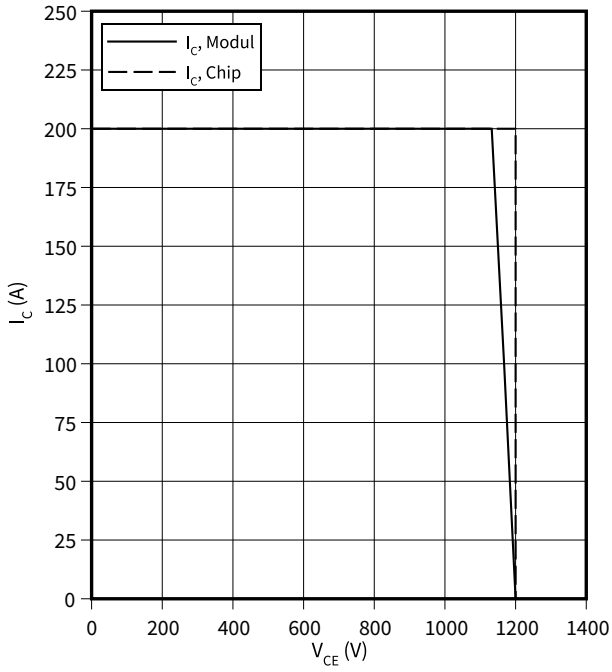
$I_C = 100\ A$, $V_{CE} = 600\ V$, $V_{GE} = \pm 15\ V$, $T_{vj} = 25\ °C$



reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$

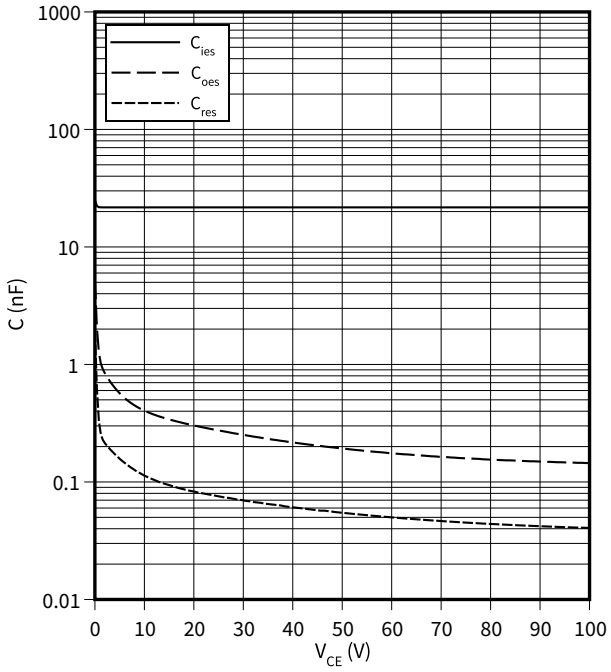
$R_{Goff} = 4.3\ \Omega$, $V_{GE} = \pm 15\ V$, $T_{vj} = 175\ °C$



capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

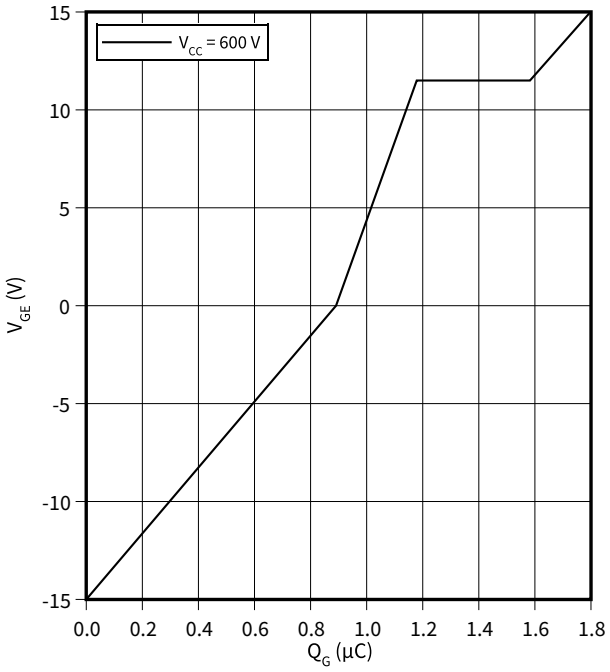
$f = 100\ kHz, V_{GE} = 0\ V, T_{vj} = 25\ °C$



gate charge characteristic (typical), IGBT, Inverter

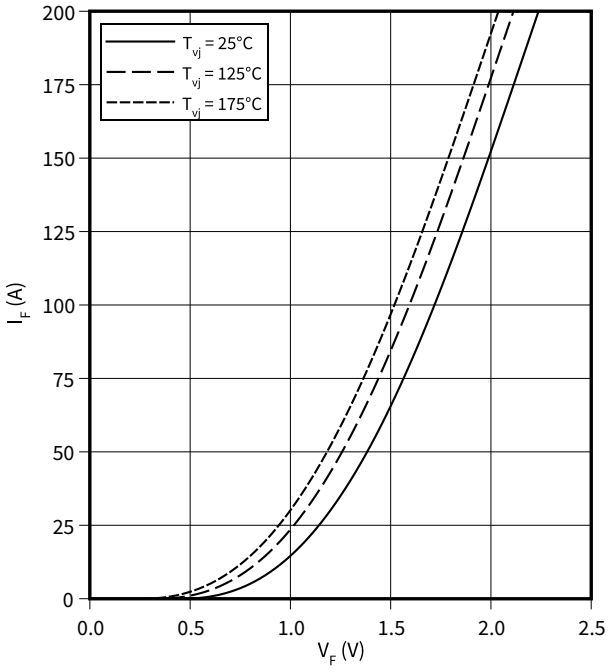
$V_{GE} = f(Q_G)$

$I_C = 100\ A, T_{vj} = 25\ °C$



forward characteristic of (typical), Diode, Inverter

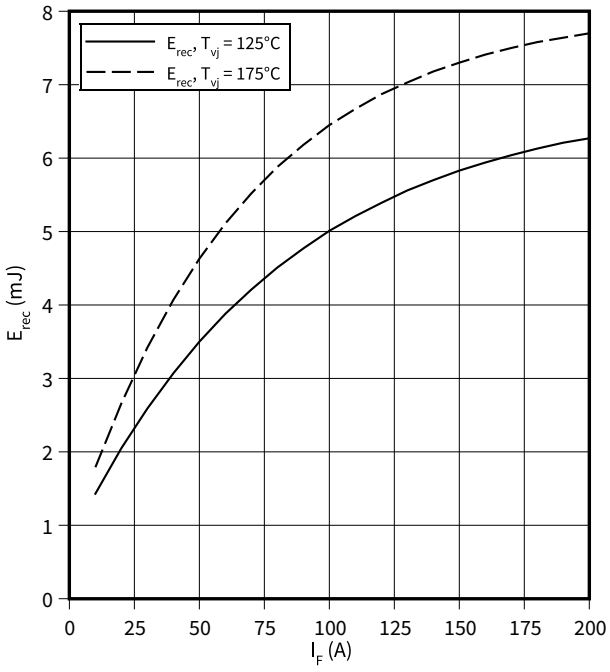
$I_F = f(V_F)$



switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

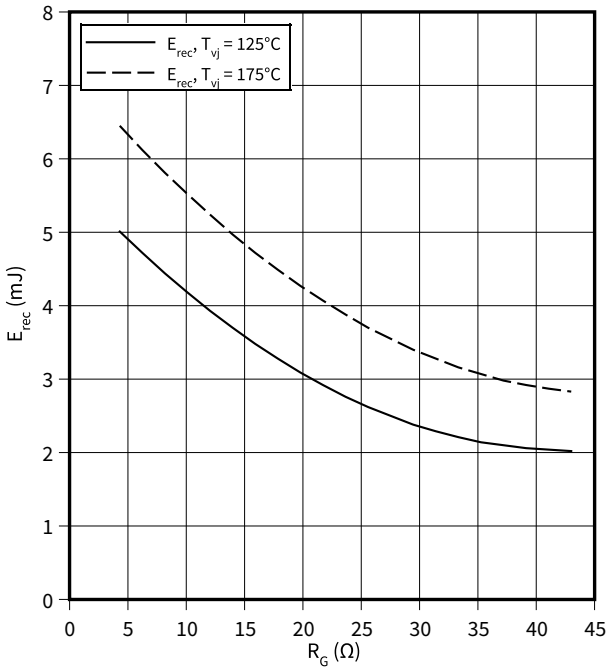
$R_{Gon} = 4.3\ \Omega, V_{CE} = 600\ V$



switching losses (typical), Diode, Inverter

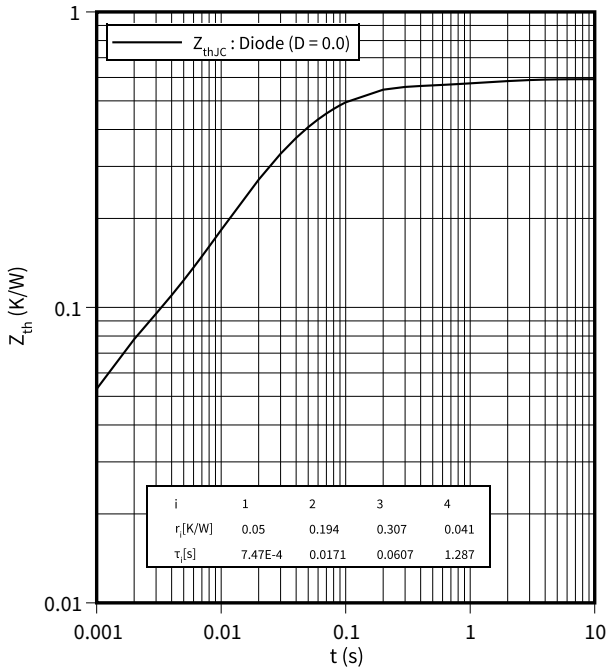
$E_{rec} = f(R_G)$

$V_{CE} = 600\ V$, $I_F = 100\ A$



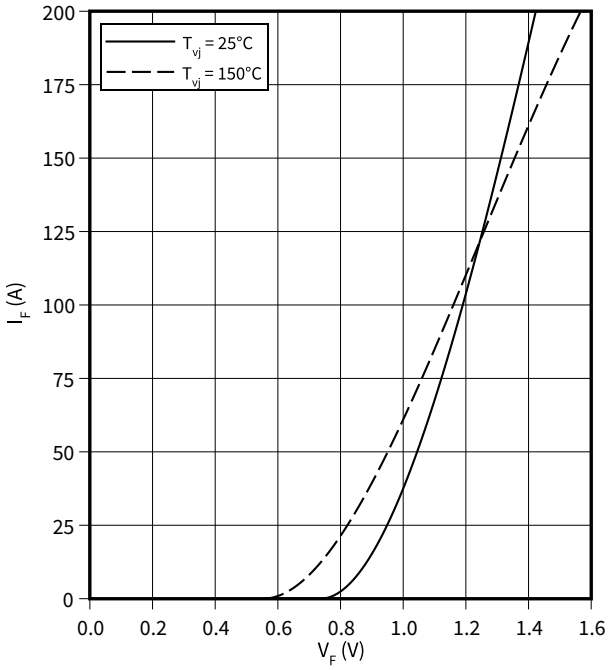
transient thermal impedance , Diode, Inverter

$Z_{th} = f(t)$



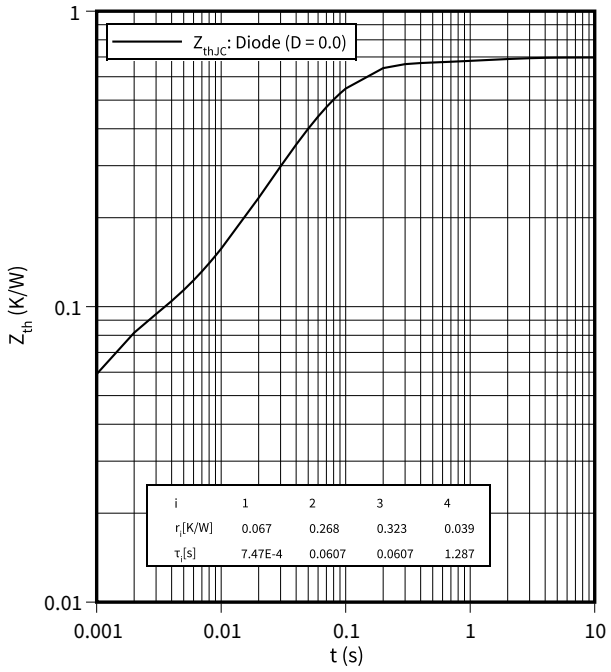
forward characteristic of (typical), Diode, Rectifier

$I_F = f(V_F)$



transient thermal impedance , Diode, Rectifier

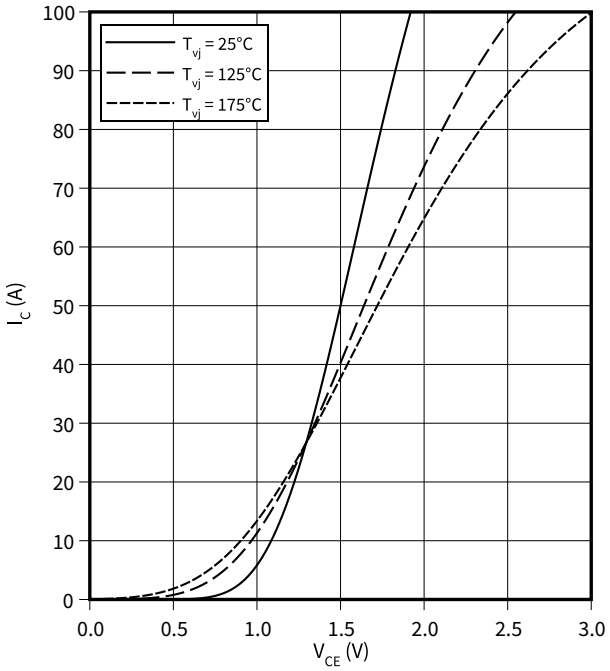
$Z_{th} = f(t)$



output characteristic (typical), IGBT, Brake-Chopper

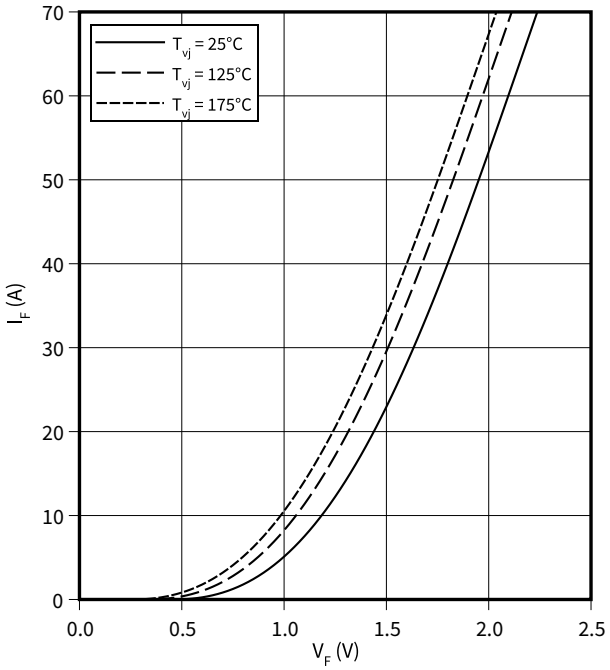
$I_C = f(V_{CE})$

$V_{GE} = 15$ V



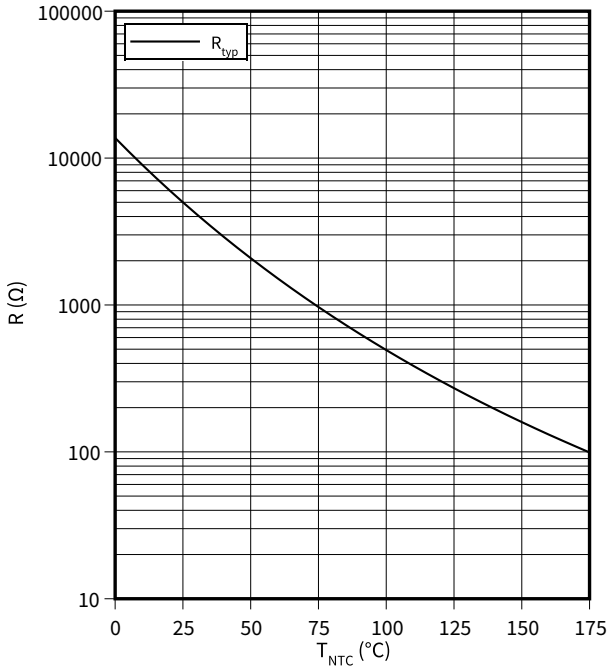
forward characteristic of (typical), Diode, Brake-Chopper

$I_F = f(V_F)$



temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



9 Circuit diagram

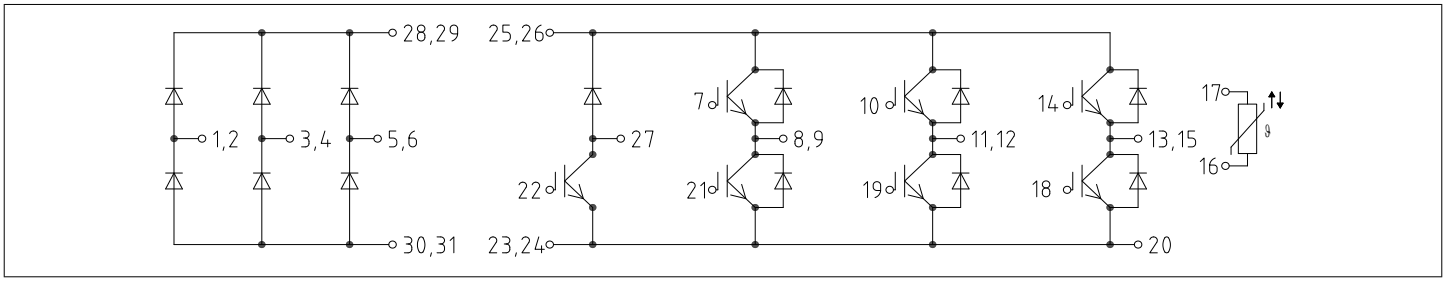


Figure 2

10 Package outlines

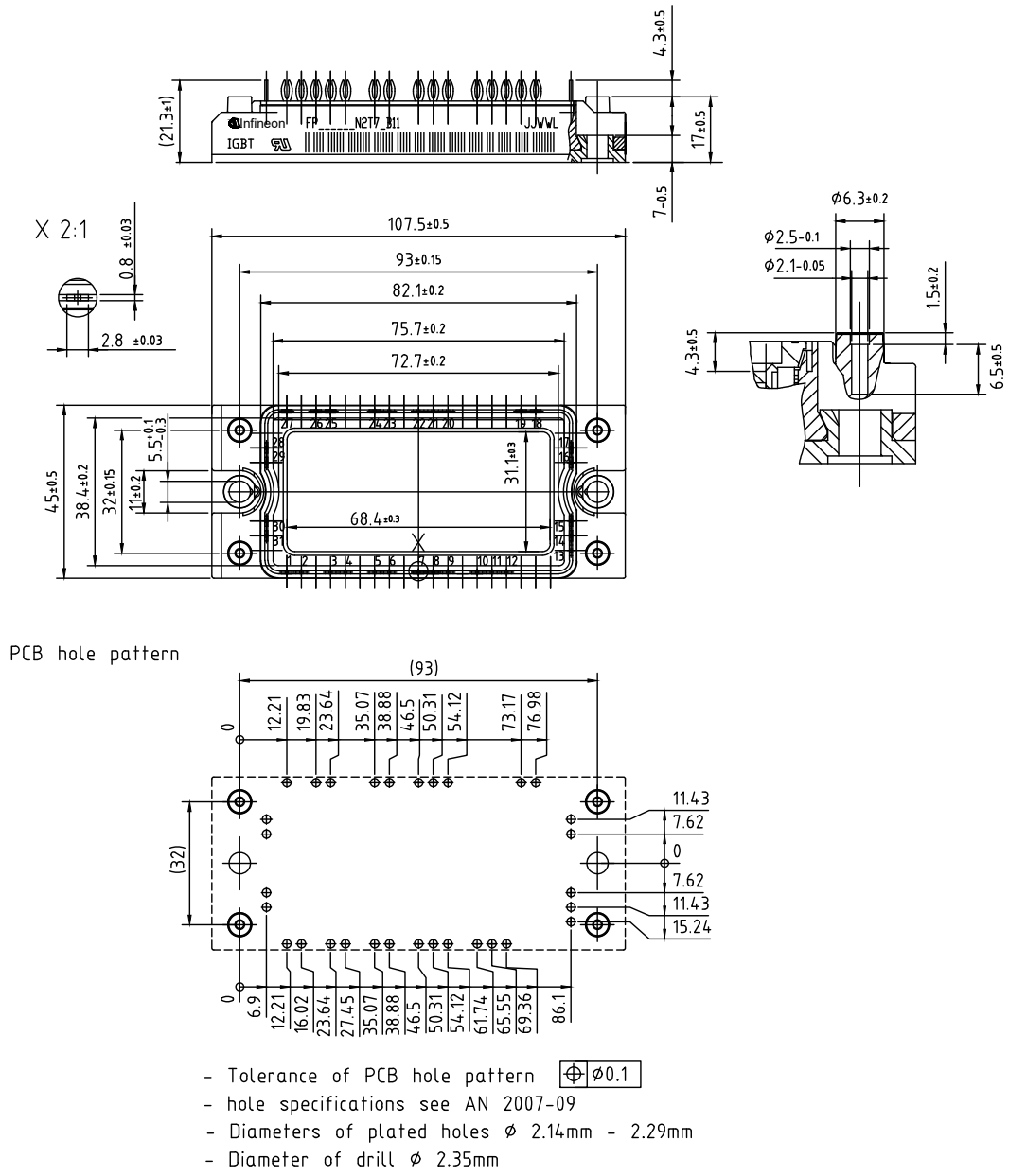


Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2021-09-21	Initial version